

## N -Channel Logic Level Enhancement Mode Power MOSFET

### Features:

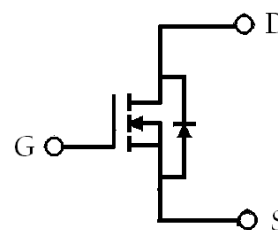
- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating package

TO-251



G D S

|   |                   |
|---|-------------------|
| <b>BV<sub>DSS</sub></b>   | <b>150V</b>       |
| <b>I<sub>D</sub>@V<sub>GS</sub>=10V, T<sub>C</sub>=25°C</b>     | <b>20A</b>        |
| <b>R<sub>DS(ON)</sub>@V<sub>GS</sub>=10V, I<sub>D</sub>=15A</b> | <b>60mΩ (typ)</b> |
| <b>R<sub>DS(ON)</sub>@V<sub>GS</sub>=5V, I<sub>D</sub>=10A</b>  | <b>59mΩ (typ)</b> |
| <b>R<sub>DS(ON)</sub>@V<sub>GS</sub>=3V, I<sub>D</sub>=3A</b>   | <b>60mΩ (typ)</b> |



G : Gate D : Drain  
 S : Source

### Ordering Information

| Device  | Package   | Shipping                  |
|---------|---|---------------------------|
| KIN6515 | TO-251<br>(RoHS compliant and halogen-free package) | 80 pcs/tube, 50 tubes/box |

### Absolute Maximum Ratings (T<sub>c</sub>=25°C, unless otherwise noted)

| Parameter  | Symbol                            | Limits   | Unit |
|--|-----------------------------------|----------|------|
| Drain-Source Voltage   | V <sub>DS</sub>                   | 150      | V    |
| Gate-Source Voltage  | V <sub>GS</sub>                   | ±16      |      |
| Continuous Drain Current @ V <sub>GS</sub> =10V, T <sub>c</sub> =25°C    | I <sub>D</sub>                    | 20       | A    |
| Continuous Drain Current @ V <sub>GS</sub> =10V, T <sub>c</sub> =100°C   |                                   | 14       |      |
| Pulsed Drain Current *1  | I <sub>DM</sub>                   | 60       |      |
| Avalanche Current  | I <sub>AS</sub>                   | 20       |      |
| Avalanche Energy @ L=0.47mH, I <sub>D</sub> =20A, R <sub>G</sub> =25Ω *3 | E <sub>AS</sub>                   | 94       | mJ   |
| Repetitive Avalanche Energy @ L=0.05mH *2                                | E <sub>AR</sub>                   | 2.5      |      |
| Total Power Dissipation @ T <sub>c</sub> =25°C                           | P <sub>D</sub>                    | 60       | W    |
| Total Power Dissipation @ T <sub>c</sub> =100°C                          |                                   | 30       |      |
| Operating Junction and Storage Temperature Range                         | T <sub>j</sub> , T <sub>stg</sub> | -55~+175 | °C   |

Note : \*1. Pulse width limited by maximum junction temperature.

\*2. Duty cycle ≤ 1%.

\*3. 100% tested by conditions of L=0.47mH, I<sub>AS</sub>=12A, V<sub>GS</sub>=10V, V<sub>DD</sub>=50V

### Thermal Data

| Parameter                                    | Symbol           | Value | Unit |
|--|------------------|-------|------|
| Thermal Resistance, Junction-to-case, max    | R <sub>θJC</sub> | 2.5   | °C/W |
| Thermal Resistance, Junction-to-ambient, max | R <sub>θJA</sub> | 100   |      |

### Characteristics (T<sub>c</sub>=25°C, unless otherwise specified)

| Symbol                    | Min. | Typ. | Max. | Unit | Test Conditions   |
|---------------------------|------|------|------|------|---|
| <b>Static</b>             |      |      |      |      |   |
| BV <sub>DSS</sub>         | 150  | -    | -    | V    | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA  |
| V <sub>GS(th)</sub>       | 0.45 | -    | 1.20 |      | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                            |
| I <sub>GSS</sub>          | -    | -    | ±100 | nA   | V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V  |
| I <sub>DSS</sub>          | -    | -    | 1    | μA   | V <sub>DS</sub> =120V, V <sub>GS</sub> =0V  |
|                           | -    | -    | 25   |      | V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C                   |
| R <sub>DS(ON)</sub> *1    | -    | 60   | 75   | mΩ   | V <sub>GS</sub> =10V, I <sub>D</sub> =15A   |
|                           | -    | 59   | 75   |      | V <sub>GS</sub> =5V, I <sub>D</sub> =10A  |
|                           | -    | 60   | 75   |      | V <sub>GS</sub> =3V, I <sub>D</sub> =3A   |
| G <sub>FS</sub> *1        | -    | 48   | -    | S    | V <sub>DS</sub> =5V, I <sub>D</sub> =10A  |
| <b>Dynamic</b>            |      |      |      |      |   |
| Q <sub>g</sub> *1, 2      | -    | 30   | -    | nC   | I <sub>D</sub> =10A, V <sub>DS</sub> =80V, V <sub>GS</sub> =5V                      |
| Q <sub>gs</sub> *1, 2     | -    | 4.8  | -    |      |   |
| Q <sub>gd</sub> *1, 2     | -    | 16   | -    |      |   |
| t <sub>d(ON)</sub> *1, 2  | -    | 23   | -    | ns   | V <sub>DS</sub> =75V, I <sub>D</sub> =1A, V <sub>GS</sub> =4.5V, R <sub>G</sub> =6Ω |
| t <sub>r</sub> *1, 2      | -    | 22   | -    |      |   |
| t <sub>d(OFF)</sub> *1, 2 | -    | 91   | -    |      |   |
| t <sub>f</sub> *1, 2      | -    | 63   | -    |      |   |

|                           |   |      |     |    |  |
|---------------------------|---|------|-----|----|--|
| Ciss                      | - | 2282 | -   | pF | V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz    |
| Coss                      | - | 120  | -   |    |  |
| Crss                      | - | 66   | -   |    |  |
| <b>Source-Drain Diode</b> |   |      |     |    |  |
| I <sub>S</sub> *1         | - | -    | 20  | A  |  |
| I <sub>SM</sub> *3        | - | -    | 60  |    |  |
| V <sub>SD</sub> *1        | - | 0.85 | 1.3 | V  | I <sub>F</sub> =I <sub>S</sub> , V <sub>GS</sub> =0V |
| trr                       | - | 50   | -   | ns | I <sub>F</sub> =20A, dI <sub>F</sub> /dt=100A/μs     |
| Qrr                       | - | 120  | -   | nC |  |

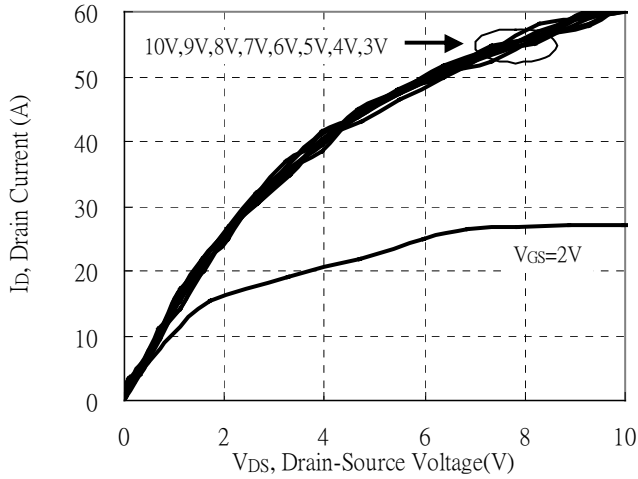
Note : \*1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

\*2.Independent of operating temperature

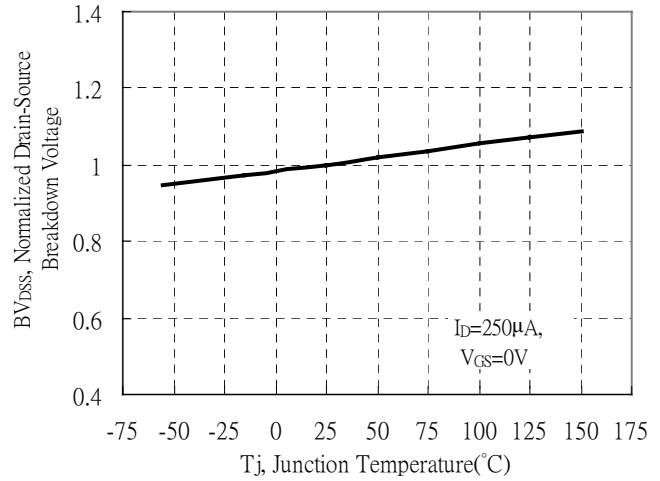
\*3.Pulse width limited by maximum junction temperature.

## Typical Characteristics

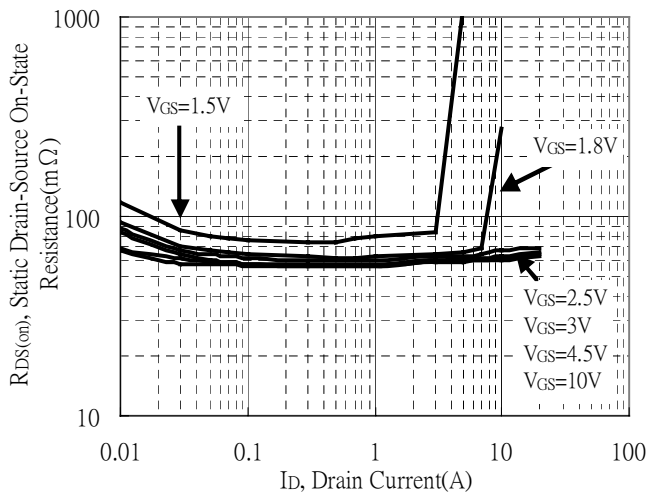
Typical Output Characteristics



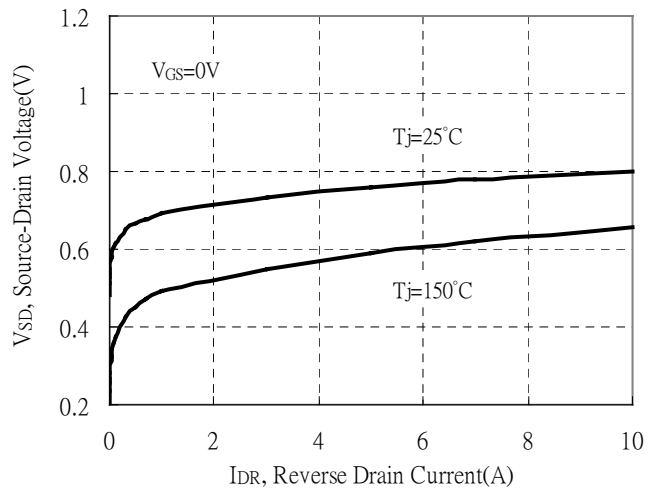
Brekdown Voltage vs Ambient Temperature



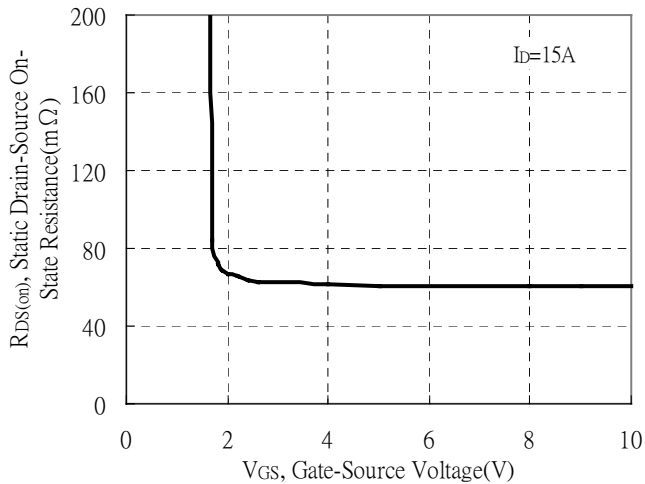
Static Drain-Source On-State resistance vs Drain Current



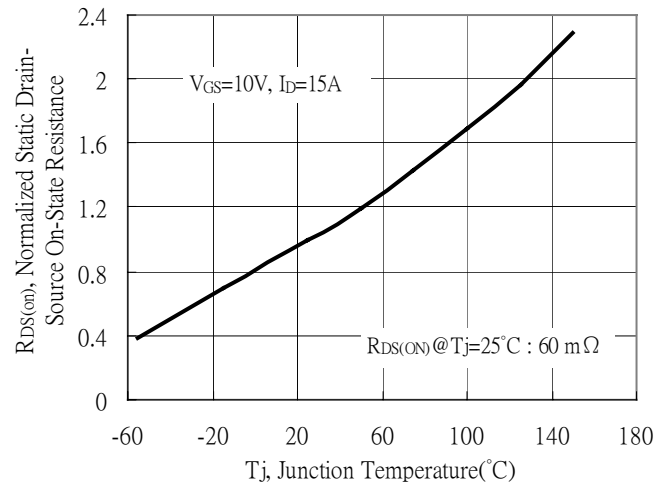
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

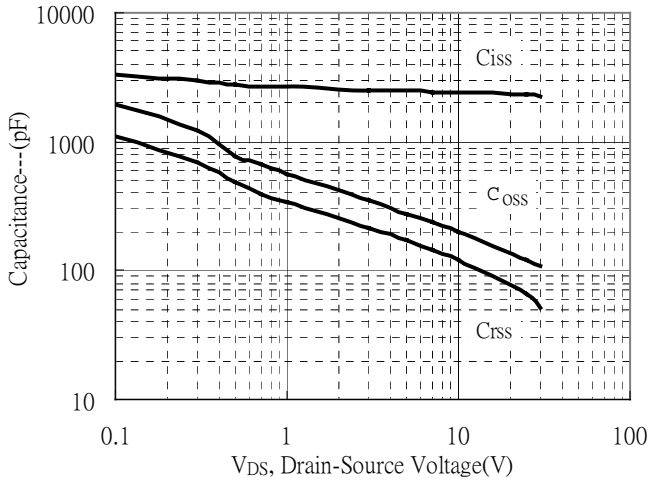


Drain-Source On-State Resistance vs Junction Temperature

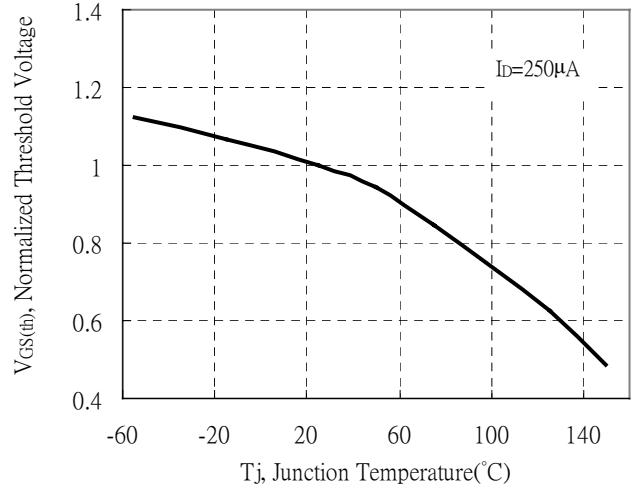


**Typical Characteristics (Cont.)**

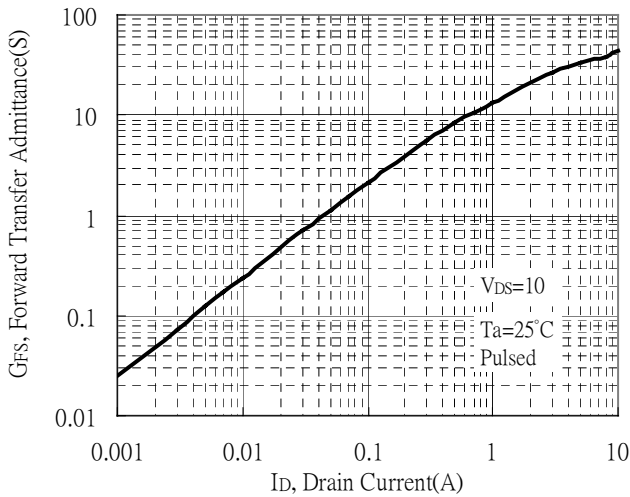
Capacitance vs Drain-to-Source Voltage



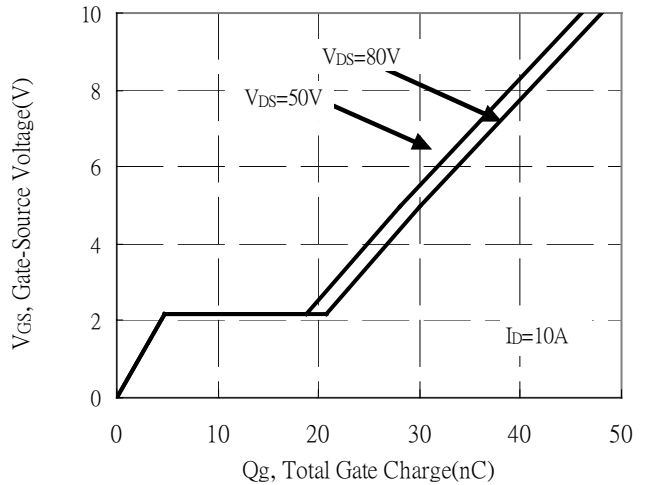
Threshold Voltage vs Junction Temperature



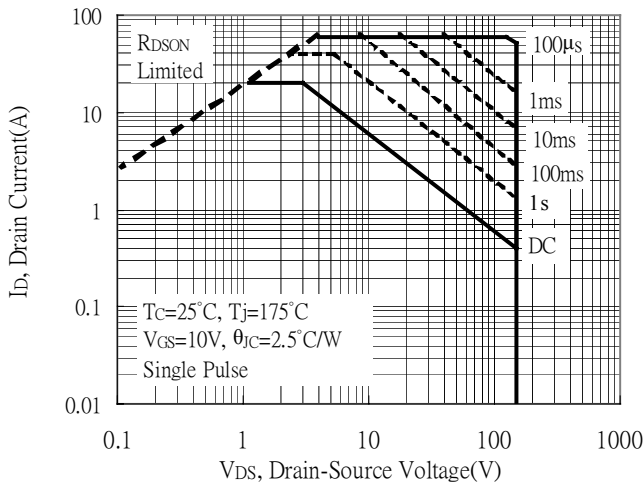
Forward Transfer Admittance vs Drain Current



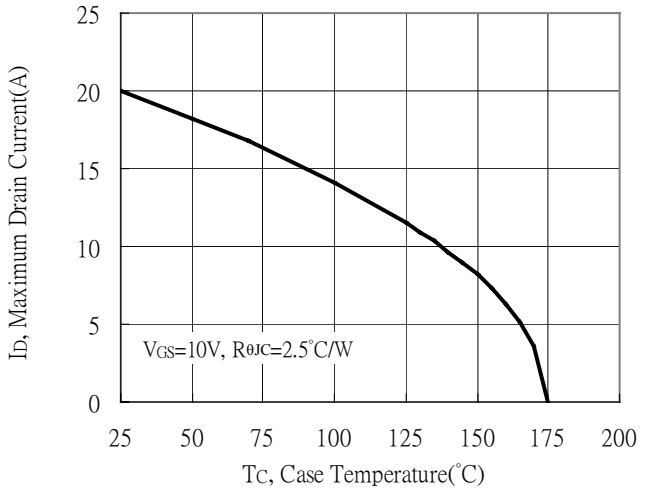
Gate Charge Characteristics



Maximum Safe Operating Area

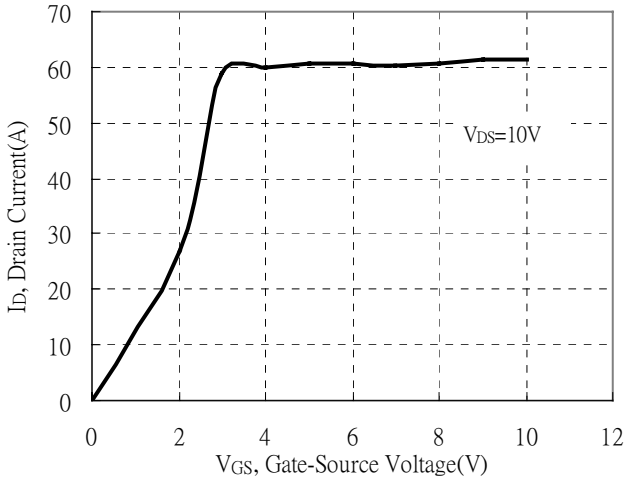


Maximum Drain Current vs Case Temperature

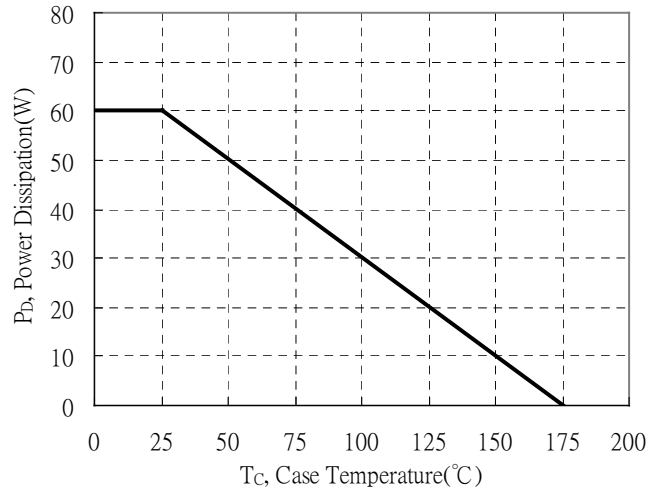


**Typical Characteristics (Cont.)**

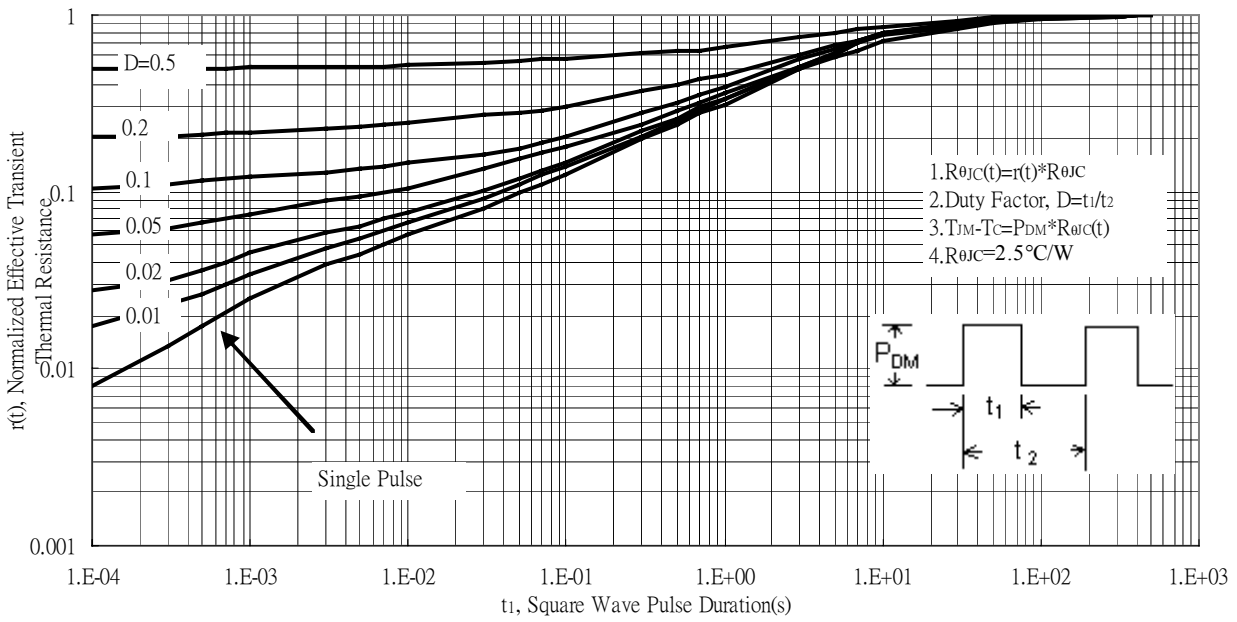
Typical Transfer Characteristics



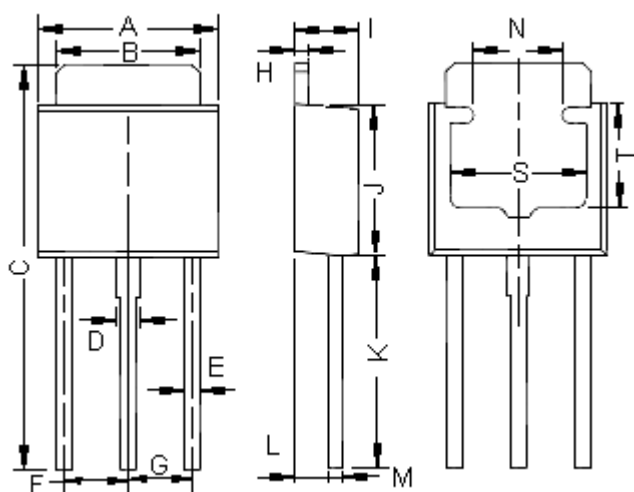
Power Derating Curve



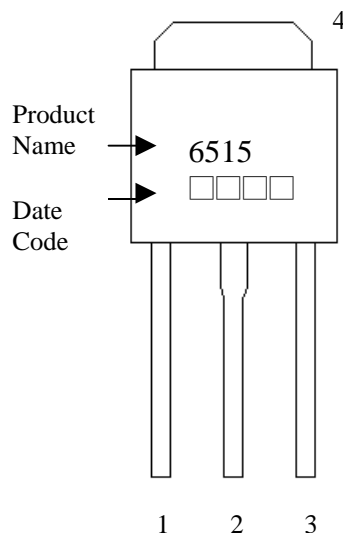
Transient Thermal Response Curves



**TO-251 Dimension**



Marking:



Style: Pin 1.Gate 2.Drain 3.Source  
 4 Drain

3-Lead TO-251 Plastic Package

| DIM | Inches |        | Millimeters |       | DIM | Inches |        | Millimeters |      |
|-----|--------|--------|-------------|-------|-----|--------|--------|-------------|------|
|     | Min.   | Max.   | Min.        | Max.  |     | Min.   | Max.   | Min.        | Max. |
| A   | 0.2500 | 0.2618 | 6.35        | 6.65  | I   | 0.0866 | 0.0945 | 2.20        | 2.40 |
| B   | 0.2047 | 0.2126 | 5.20        | 5.40  | J   | 0.2126 | 0.2244 | 5.40        | 5.70 |
| C   | 0.5709 | 0.5866 | 14.50       | 14.90 | K   | 0.2992 | 0.3071 | 7.60        | 7.80 |
| D   | 0.0276 | 0.0354 | 0.70        | 0.90  | L   | 0.0453 | 0.0492 | 1.15        | 1.25 |
| E   | 0.0199 | 0.0276 | 0.50        | 0.70  | M   | 0.0169 | 0.0228 | 0.43        | 0.58 |
| F   | 0.0886 | 0.0925 | 2.25        | 2.35  | N   | 0.1181 | REF    | 3.00        | REF  |
| G   | 0.0886 | 0.0925 | 2.25        | 2.35  | S   | 0.1969 | REF    | 5.00        | REF  |
| H   | 0.0169 | 0.0228 | 0.43        | 0.58  | T   | 0.1496 | REF    | 3.80        | REF  |